REMARKS/ARGUMENTS

Favorable reconsideration of this application as currently amended and in light of the following discussion is respectfully requested.

Claims 1-4 remain pending, with Claims 1-3 being presently active in this application,
Claim 4 having been previously withdrawn from consideration. By the present amendment
Claim 1 having been amended and Claim 5 is newly added.

In the outstanding Office Action Claims 1-3 were rejected under 35 U.S. C. 103(a) as being unpatentable over <u>Spierings</u> (6,045,715) in view of <u>Niwayama</u> (JP-09027469A.

In light of the outstanding rejection, Claim 1 have been amended to clarify the claim invention and thereby more clearly patentably define over the cited prior art references. To that end, the Claim 1 have been amended to clarify that the first etching solution removing small defects or micro-cracks on a surface of said substrate from the surface of said glass substrates and said second etching solution making said glass substrate as thin as desirable. Support for the changes to Claim 1 is found at page 7, lines 15-16 if the specification. Claim 5, newly added to clarify that the method of manufacturing a liquid crystal display device according to claim 1, wherein said first etching solution is used at a normal temperature but said second etching solution is used at a higher temperature than such the normal temperature. Support for this newly added Claim 5 is found at Page 6, lines 8-11 of the specification.

Spierings disclose at Claim 4, lines 20-22 in U.S. Patent 6,045,715 that "etching rates which are not too high are preferred for pattern" and Claim 5, lines 33-36 in U.S. Patent 6,045,715, "For deeper pit, for example, a longer etching time is preferably used. For narrow patterns, an etchant which is not too strong is preferably used for the etching treatment." Therefore, <u>Spierings</u> suggest the etching rate is slower and etching solution is weaker for

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removing small defects or micro-cracks. Therefore, Spierings suggest the etching rate is

slower and etching solution is weaker for removing small defects or micro-cracks.

On the other hand, Niwayama describes "To avoid transferring foreign matter or

depositing dust to the surface of a semiconductor substrate" in Japanese 09027469.

Furthermore, Niwayama discloses a method for preventing attachment of foreign particles or

the like on an oxide and removing the oxide by etching.

Accordingly, from above discussion described, it is respectfully submitted that Claim

1 and its dependent Claims 2 and 3 are patentable over 2 and 3 are patentable over Spierings

and/or Niwayama.

Consequently, in view of the above comments, the pending claims are believed to be

patentably distinguishing over the cited prior art and in condition for allowance. An early

and favorable action to that effect is respectfully requested.

Respectfully submitted,

Customer Number

22850

Tel: (703) 413-3000 Fax: (703) 413 -2220

(OSMMN 08/07)

OBLON, SPIVAK, McCLELLAND,

MATER & NEUSTADT, P.C.

Eckhard H. Kuesters

Attorney of Record

Registration No. 28,870

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